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CZT5338
NPN SILICON
POWER TRANSISTOR

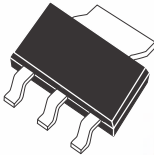
Central

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT5338 type is an NPN silicon power transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high current amplification and switching capability.

POWER
223TM



SOT-223 CASE

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	100	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	5.0	A
Base Current	I _B	1.0	A
Power Dissipation	P _D	2.0	W
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	62.5	°C/W

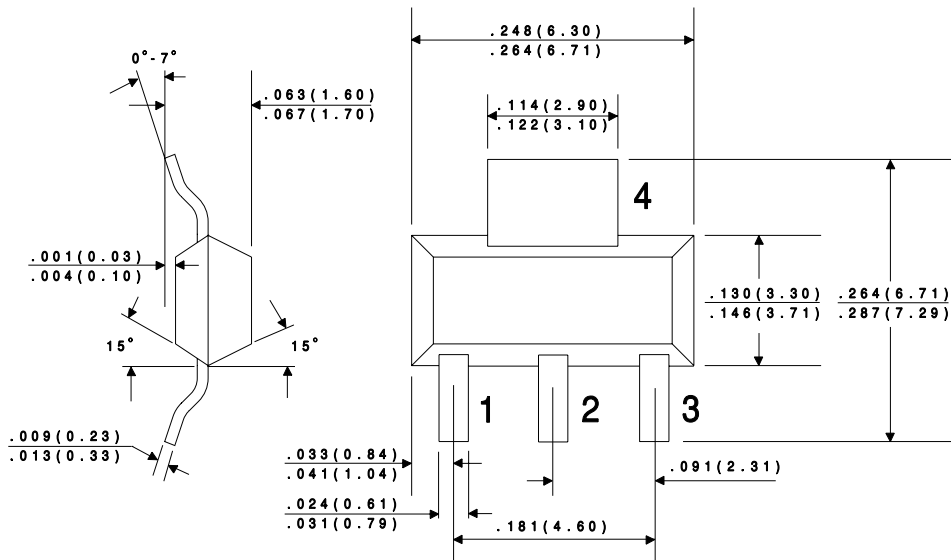
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CB0}	V _{CB} =100V		10	μA
I _{EBO}	V _{BE} =6.0V		100	μA
I _{CEO}	V _{CE} =90V		100	μA
BV _{CEO}	I _C =50mA	100		V
V _{CE(SAT)}	I _C =2.0A, I _B =200mA		0.7	V
V _{CE(SAT)}	I _C =5.0A, I _B =500mA		1.2	V
V _{BE(SAT)}	I _C =2.0A, I _B =200mA		1.2	V
V _{BE(SAT)}	I _C =5.0A, I _B =500mA		1.8	V
h _{FE}	V _{CE} =2.0V, I _C =500mA	30		
h _{FE}	V _{CE} =2.0V, I _C =2.0A	30	120	
h _{FE}	V _{CE} =2.0V, I _C =5.0A	20		



SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=10V, I_C=500mA, f=10MHz$	30		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		250	pF
C_{ib}	$V_{BE}=2.0V, I_C=0, f=1.0MHz$		1000	pF
t_d	$V_{CC}=40V, V_{BE}=3.0V, I_C=2.0A, I_{B1}=200mA$		100	ns
t_r	$V_{CC}=40V, V_{BE}=3.0V, I_C=2.0A, I_{B1}=200mA$		100	ns
t_s	$V_{CC}=40V, I_C=2.0A, I_{B1}=I_{B2}=200mA$		2.0	μs
t_f	$V_{CC}=40V, I_C=2.0A, I_{B1}=I_{B2}=200mA$		200	ns

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR